

Serial No. 10/807,729

Amendment B

REMARKS

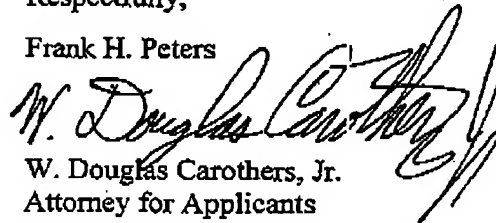
In a conversation with the Examiner today, concern was expressed by the undersigned about the similarities in a claim in this application with a claim in patent US 6,771,682 B2, in particular, the concern was between claim 1 in this application and claim 47 in issued patent '682 with an eye to avoid double patenting, particularly when considering claims 15 and 17, dependent from claim 1, in this application with the patent '682 claim 47. The differences between claims 1 and 47 are set forth in Section A above.

It can be seen in the comparison of Section A that claim 1 in this application differs further from patent '682 claim 47 in not requiring a limitation of a surface region of the electrical isolation region where the bias point is located. Also, claim 47 requires, and claim 1 herein does not require, a plurality of semiconductor layers. Therefore, it is submitted that there is no issue of double patenting because claim 1 herein does not include these limitations found in claim 47 of patent '682.

As to Section 2 above, there is no antecedent basis for "via some of the semiconductor layers" as well as "the bias point" in original claim 1 so that the amendments of claim 1 cure these matters. It is requested that the amendments to claim 1 be entered of record.

Respectfully,

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